

**Silicon PNP Power Transistors**

**2SA1095**

**DESCRIPTION**

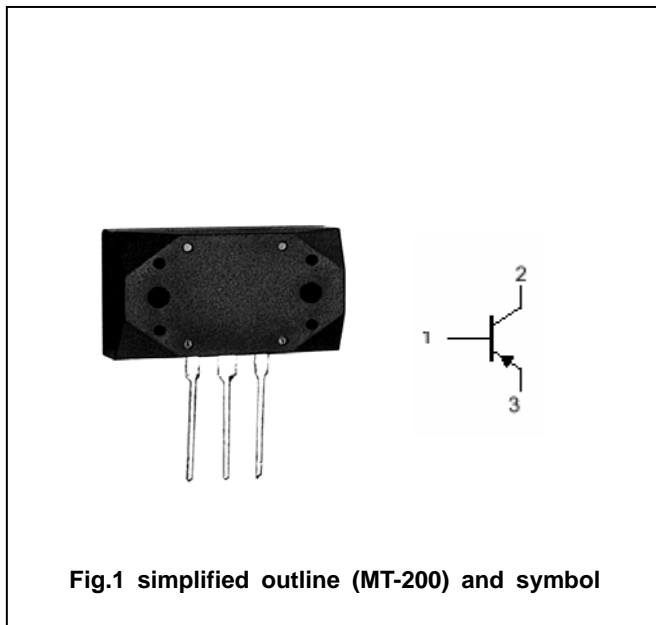
- With MT-200 package
- Complement to type 2SC2565
- High breakdown voltage
- High transition frequency

**APPLICATIONS**

- Power amplifier applications
- Recommended for 100W high-fidelity audio frequency amplifier output stage

**PINNING(see Fig.2)**

| PIN | DESCRIPTION                          |
|-----|--------------------------------------|
| 1   | Base                                 |
| 2   | Collector;connected to mounting base |
| 3   | Emitter                              |



**Absolute maximum ratings (Ta=25°C)**

| SYMBOL           | PARAMETER                   | CONDITIONS           | VALUE   | UNIT |
|------------------|-----------------------------|----------------------|---------|------|
| V <sub>CBO</sub> | Collector-base voltage      | Open emitter         | -160    | V    |
| V <sub>CEO</sub> | Collector-emitter voltage   | Open base            | -160    | V    |
| V <sub>EBO</sub> | Emitter-base voltage        | Open collector       | -5      | V    |
| I <sub>C</sub>   | Collector current           |                      | -15     | A    |
| I <sub>E</sub>   | Emitter current             |                      | 15      | A    |
| P <sub>C</sub>   | Collector power dissipation | T <sub>C</sub> =25°C | 150     | W    |
| T <sub>j</sub>   | Junction temperature        |                      | 150     | °C   |
| T <sub>stg</sub> | Storage temperature         |                      | -55~150 | °C   |

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## 2SA1095

## CHARACTERISTICS

T<sub>j</sub>=25°C unless otherwise specified

| SYMBOL               | PARAMETER                            | CONDITIONS                                       | MIN  | TYP. | MAX  | UNIT |
|----------------------|--------------------------------------|--|------|------|------|------|
| V <sub>(BR)CEO</sub> | Collector-emitter breakdown voltage  | I <sub>C</sub> =-100mA; I <sub>B</sub> =0        | -160 |      |      | V    |
| V <sub>(BR)EBO</sub> | Emitter-base breakdown voltage       | I <sub>E</sub> =-10mA; I <sub>C</sub> =0         | -5   |      |      | V    |
| V <sub>CEsat</sub>   | Collector-emitter saturation voltage | I <sub>C</sub> =-5 A; I <sub>B</sub> =-0.5 A     |      |      | -2.0 | V    |
| V <sub>BE</sub>      | Base-emitter on voltage              | I <sub>C</sub> =-5A ; V <sub>CE</sub> =-5V       |      |      | -2.0 | V    |
| I <sub>CBO</sub>     | Collector cut-off current            | V <sub>CB</sub> =-160V; I <sub>E</sub> =0        |      |      | -50  | μ A  |
| I <sub>EBO</sub>     | Emitter cut-off current              | V <sub>EB</sub> =-5V; I <sub>C</sub> =0          |      |      | -50  | μ A  |
| h <sub>FE-1</sub>    | DC current gain                      | I <sub>C</sub> =-1A ; V <sub>CE</sub> =-5V       | 55   |      | 240  |      |
| h <sub>FE-2</sub>    | DC current gain                      | I <sub>C</sub> =-5A ; V <sub>CE</sub> =-5V       | 40   |      |      |      |
| f <sub>T</sub>       | Transition frequency                 | I <sub>C</sub> =-1A ; V <sub>CE</sub> =-10V      |      | 60   |      | MHz  |
| C <sub>OB</sub>      | Output capacitance                   | I <sub>E</sub> =0; V <sub>CB</sub> =-10V; f=1MHz |      | 350  |      | pF   |

◆ h<sub>FE</sub> classifications

| R      | O      | Y       |
|--------|--------|---------|
| 55-110 | 80-160 | 120-240 |

PACKAGE OUTLINE

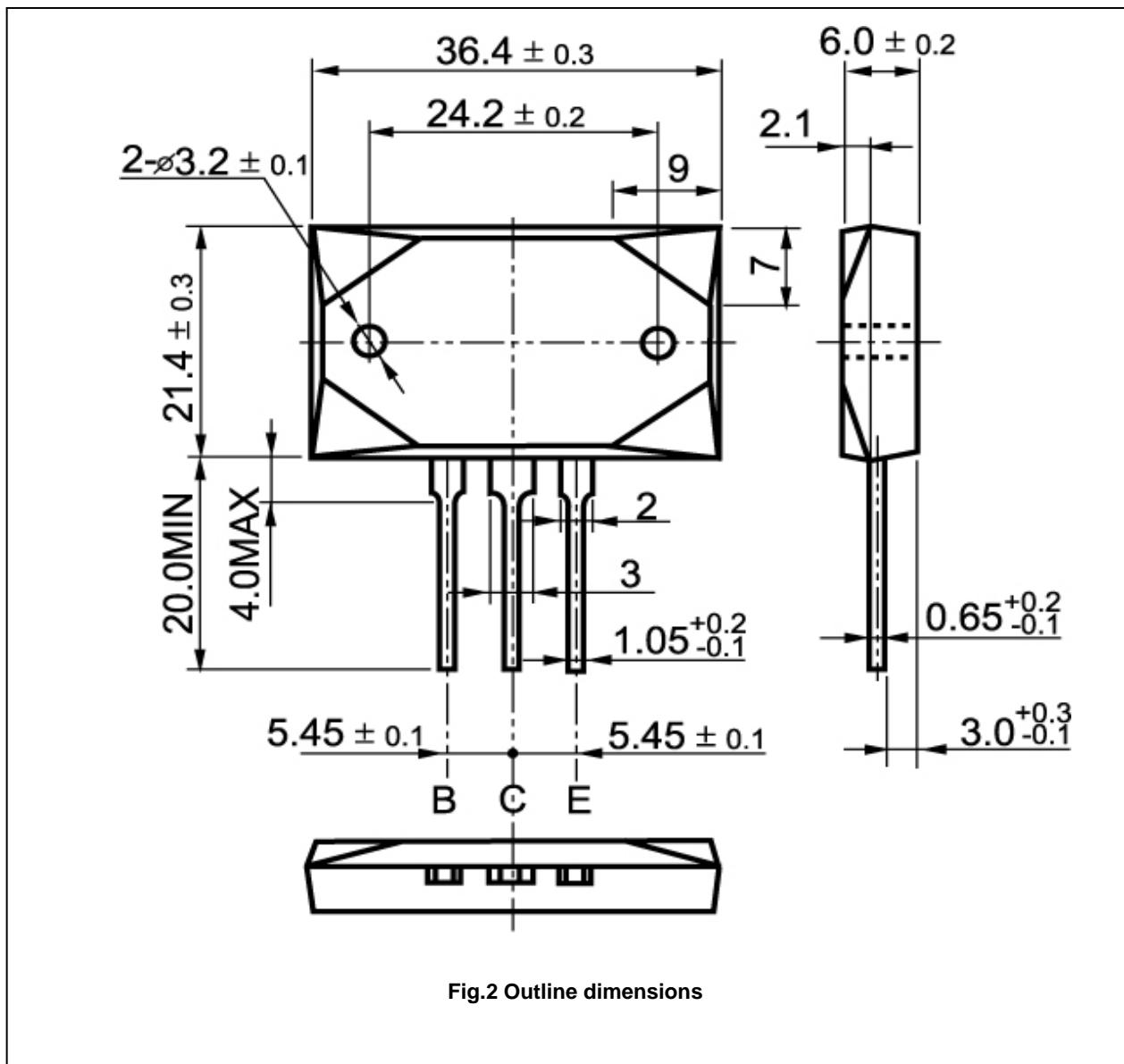


Fig.2 Outline dimensions